## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroshi YAMADA et al.

Application No.: 10/542,147

Filed: September 6, 2005

For:

PHOTOELECTRIC TRANSDUCER, PHOTOELECTRIC TRANSDUCER APPARATU

AND IRON SILICIDE FILM

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- This Information Disclosure Statement is being filed (a) within three months of 冈 the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 冈 2. Relevance of the references 2-3 is discussed in the present specification.
- 図 3. References 1, 4-13 were cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- 冈 In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent 4. application publications are not attached.
- 冈 5. English language Abstracts of the non-English language references are attached hereto. An English language translation of Reference 13 is attached hereto.

 $\boxtimes$ Computer-generated English language translations of the following Japanese references have been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and are attached, but have not been reviewed for accuracy. See

References 3, 5-8 and 11-12.

stration No. 27,075

Philip A. Caramanica, Jr. Registration No. 51,528

JAO:PAC/nxy

Date: September 6, 2005

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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 124683			APPLICATION NO. 10/542,147			
FILING DATE   GROUP   2816	INFORMATION DISCLOSURE STATEMENT										
September 6, 2005   2816	(Use several sheets if necessary)										
U.S. PATENT DOCUMENTS											
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FOREIGN PATENT DOCUMENTS    DOCUMENT NUMBER   DATE   COUNTRY   CLASS   CLASS			DOCUMENT NUMBER	DATE		NAME	·		CLASS		
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